



# UF5400 - UF5408

## ULTRAFAST RECOVERY RECTIFIER DIODES

**VOLTAGE RANGE: 50 - 1000V**

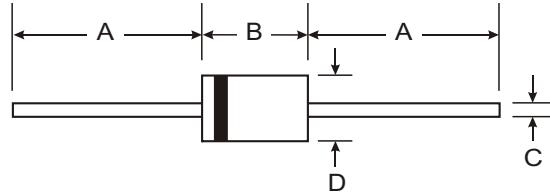
**CURRENT: 3.0 A**

### Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

### Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-201AD		
Dim	Min	Max
A	25.40	—
B	8.50	9.53
C	0.96	1.06
D	4.80	5.21

All Dimensions in mm

### Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	UF 5400	UF 5401	UF 5402	UF 5403	UF 5404	UF 5406	UF 5407	UF 5408	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>									
Working Peak Reverse Voltage	V <sub>RWM</sub>	50	100	200	300	400	600	800	1000	V
DC Blocking Voltage	V <sub>R</sub>									
RMS Reverse Voltage	V <sub>R(RMS)</sub>	35	70	140	210	280	420	560	700	V
Average Rectified Output Current (Note 1)	I <sub>O</sub>									A
$\text{@ } T_A = 55^\circ\text{C}$										
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>									A
Forward Voltage $\text{@ } I_F = 3.0\text{A}$	V <sub>FM</sub>									V
Peak Reverse Current $\text{@ } T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage $\text{@ } T_A = 100^\circ\text{C}$	I <sub>RM</sub>									$\mu\text{A}$
Reverse Recovery Time (Note 2)	t <sub>rr</sub>									nS
Typical Junction Capacitance (Note 3)	C <sub>j</sub>									pF
Operating Temperature Range	T <sub>j</sub>						-65 to +125			$^\circ\text{C}$
Storage Temperature Range	T <sub>STG</sub>						-65 to +150			$^\circ\text{C}$

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.

3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

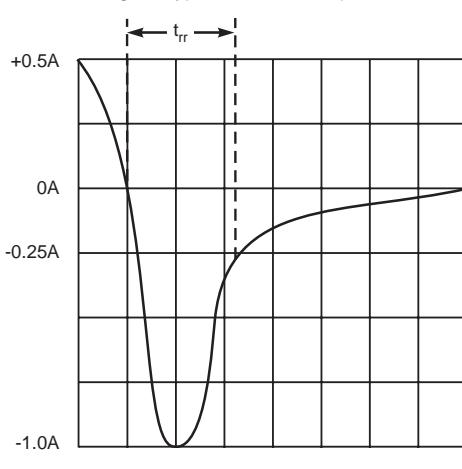
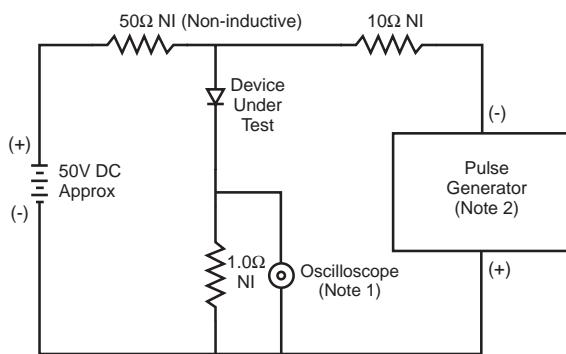
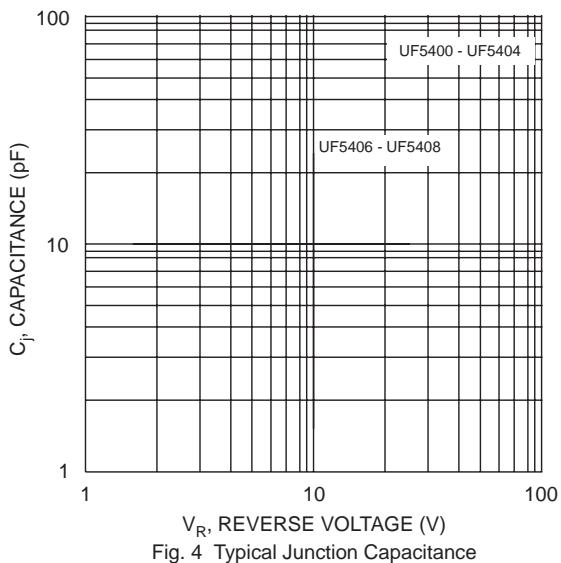
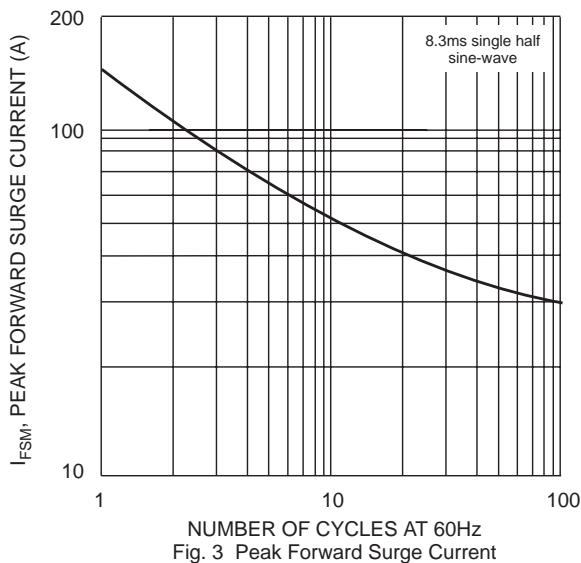
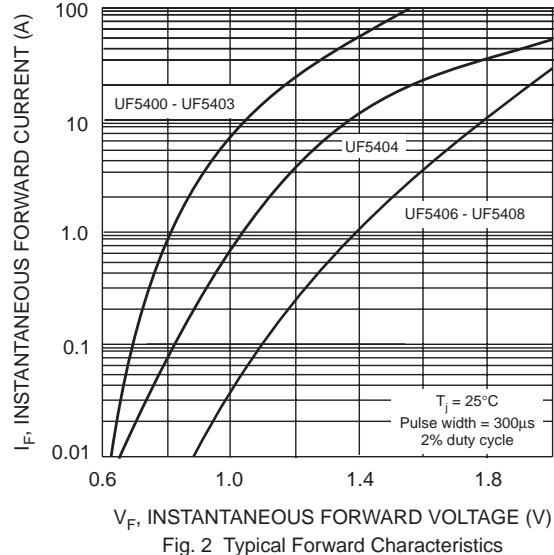
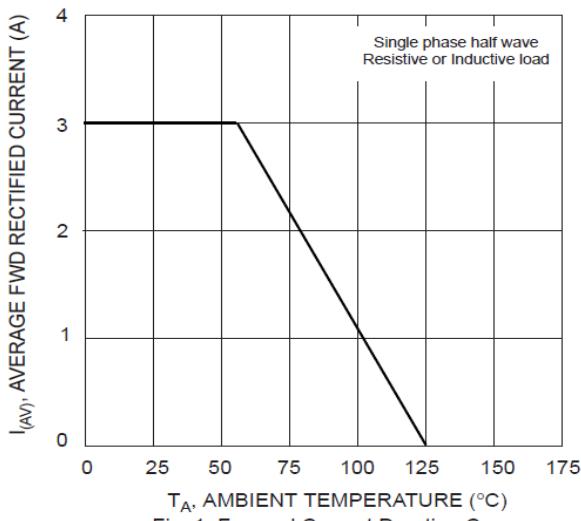


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit